

TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL MOS TYPE (π -MOSV)

YTA630

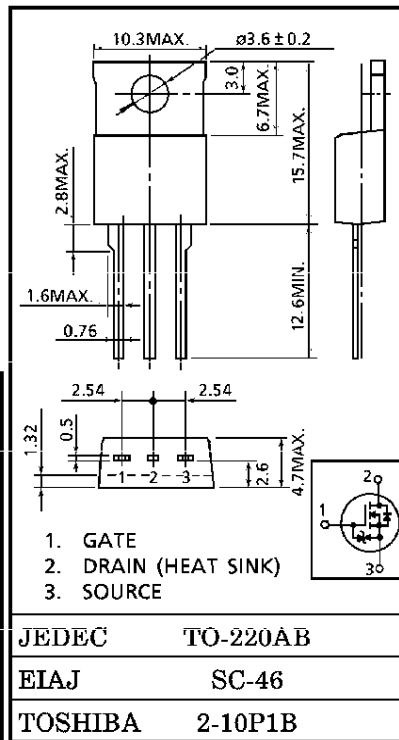
HIGH SPEED, HIGH VOLTAGE SWITCHING APPLICATIONS
 SWITCHING REGULATOR, DC-DC CONVERTER AND MOTOR DRIVE
 APPLICATIONS

INDUSTRIAL APPLICATIONS
 Unit in mm

- Low Drain-Source ON Resistance : $R_{DS(ON)} = 0.26\Omega$ (Typ.)
- High Forward Transfer Admittance : $|Y_{fs}| = 8S$ (Typ.)
- Low Leakage Current : $I_{DSS} = 100\mu A$ (Max.) ($V_{DS} = 200V$)
- Enhancement-Mode : $V_{th} = 1.5 \sim 3.5V$ ($V_{DS} = 10V, I_D = 1mA$)

MAXIMUM RATINGS ($T_a = 25^\circ C$)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Drain-Source Voltage		V_{DSS}	200	V
Drain-Gate Voltage ($R_{GS} = 20k\Omega$)		V_{DGR}	200	V
Gate-Source Voltage		V_{GSS}	± 20	V
Drain Current	DC	I_D	10	A
	Pulse	I_{DP}	40	A
Drain Power Dissipation ($T_c = 25^\circ C$)		P_D	40	W
Single Pulse Avalanche Energy**		E_{AS}	98	mJ
Avalanche Current		I_{AR}	10	A
Repetitive Avalanche Energy*		E_{AR}	4	mJ
Channel Temperature		T_{ch}	150	$^\circ C$
Storage Temperature Range		T_{stg}	$-55 \sim 150$	$^\circ C$



Weight : 2.0g

THERMAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance, Channel to Case	$R_{th(ch-c)}$	3.125	$^\circ C / W$
Thermal Resistance, Channel to Ambient	$R_{th(ch-a)}$	83.3	$^\circ C / W$

Note ;

- * Repetitive rating ; Pulse Width Limited by Max. junction temperature.
- ** $V_{DD} = 50V, T_{ch} = 25^\circ C, L = 1.58mH, R_G = 25\Omega, I_{AR} = 10A$

**This transistor is an electrostatic sensitive device.
 Please handle with caution.**

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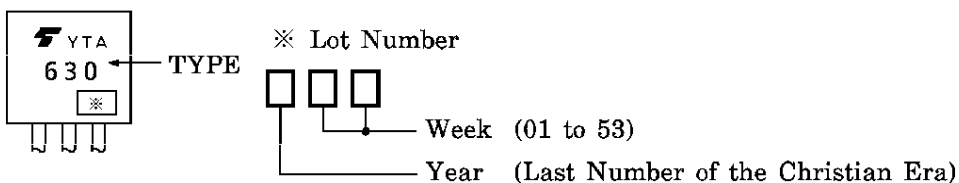
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

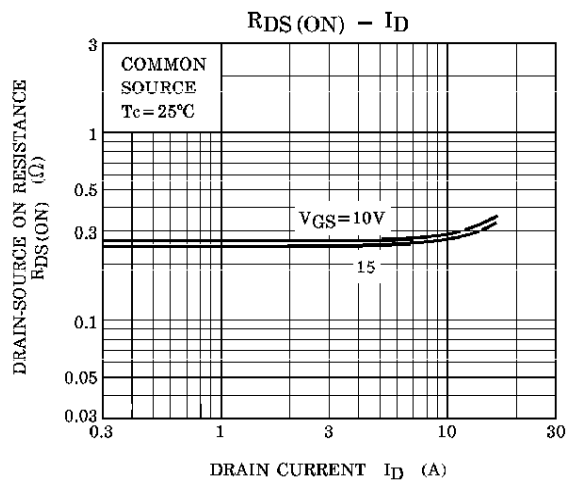
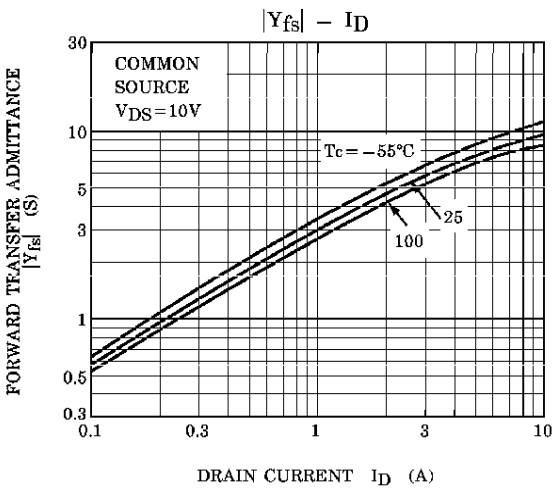
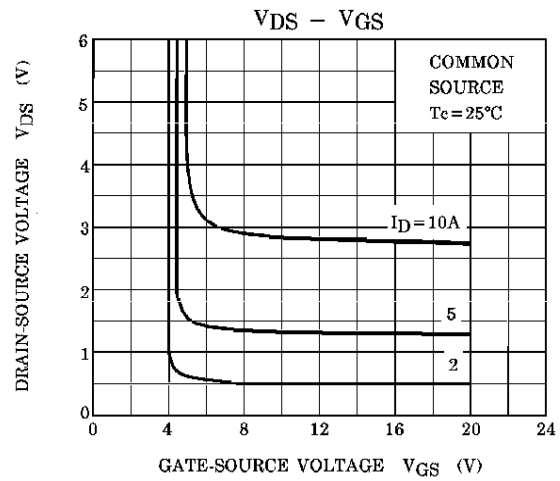
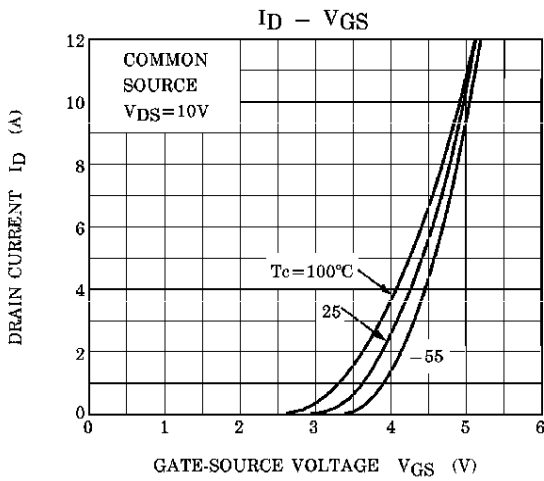
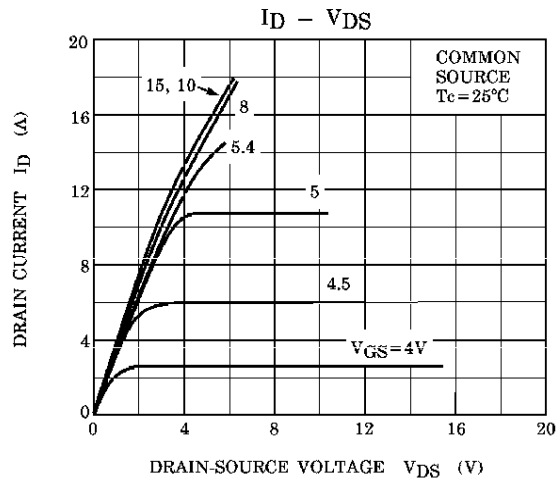
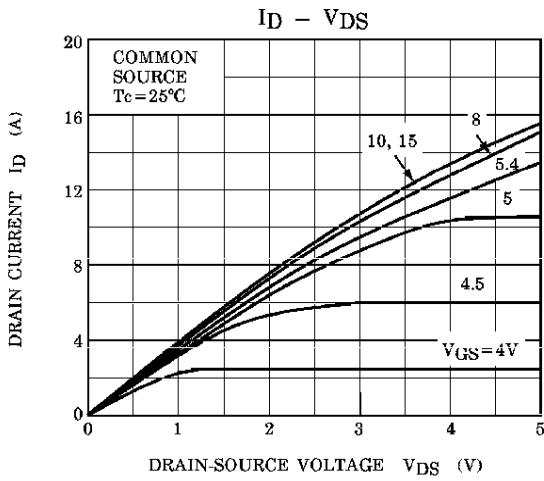
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT	
Gate Leakage Current	I_{GSS}	$V_{GS} = +16V, V_{DS} = 0V$	—	—	+10	μA	
Drain Cut-off Current	I_{DSS}	$V_{DS} = 200V, V_{GS} = 0V$	—	—	100	μA	
Gate-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = 10mA, V_{GS} = 0V$	200	—	—	V	
Gate Threshold Voltage	V_{th}	$V_{DS} = 10V, I_D = 1mA$	1.5	—	3.5	V	
Drain-Source ON Resistance	$R_{DS(ON)}$	$V_{GS} = 10V, I_D = 5A$	—	0.26	0.4	Ω	
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = 10V, I_D = 5A$	4	8	—	S	
Input Capacitance	C_{iss}	$V_{DS} = 10V, V_{GS} = 0V$ $f = 1MHz$	—	700	—	pF	
Reverse Transfer Capacitance	C_{rss}		—	80	—		
Output Capacitance	C_{oss}		—	270	—		
Switching Time	Rise Time	t_r		—	15	—	ns
	Turn-on Time	t_{on}		—	25	—	
	Fall Time	t_f		—	15	—	
	Turn-off Time	t_{off}		$V_{IN} : t_r, t_f < 5ns,$ $Duty \leq 1\%, t_w = 10\mu s$	—	70	
Total Gate Charge (Gate-Source Plus Gate-Drain)	Q_g	$V_{DD} \doteq 160V, V_{GS} = 10V$ $I_D = 10A$	—	17	—	nC	
Gate-Source Charge	Q_{gs}		—	10	—		
Gate-Drain ("Miller") Charge	Q_{gd}		—	7	—		

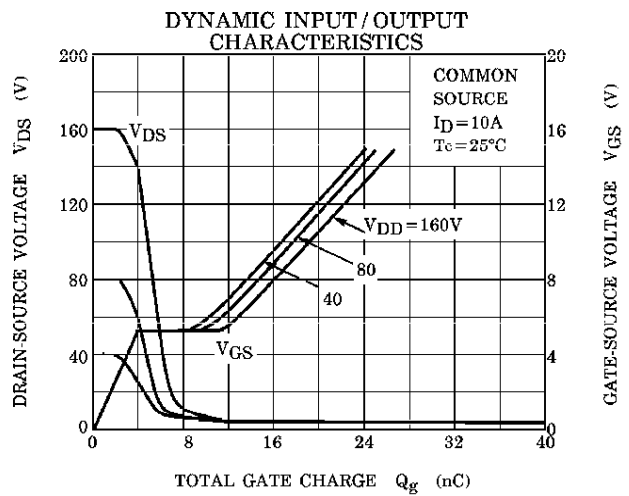
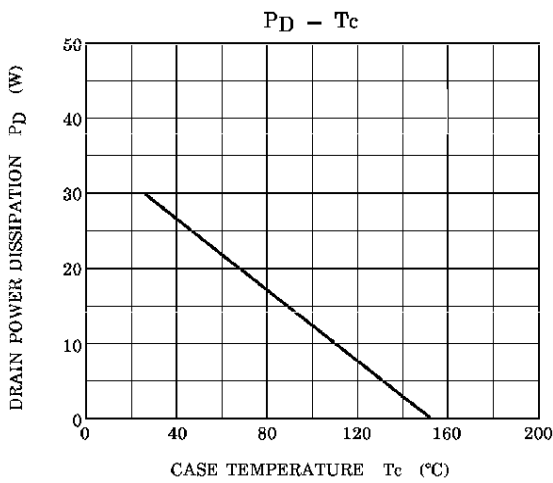
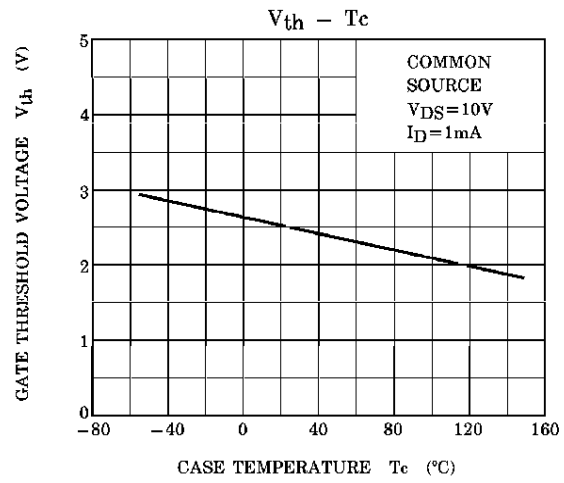
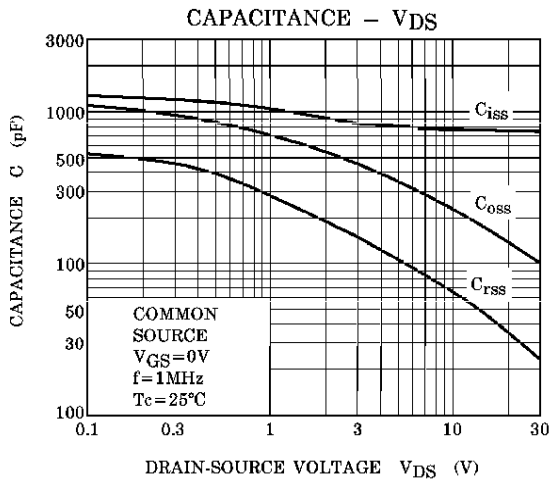
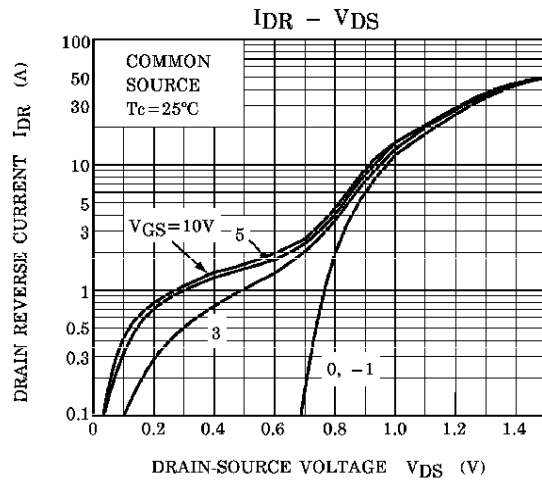
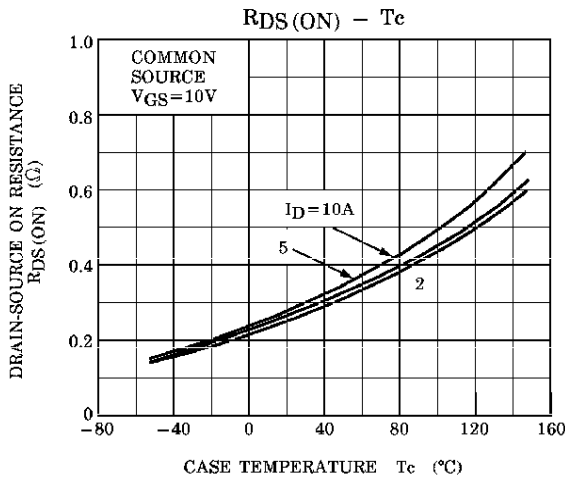
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (Ta = 25°C)

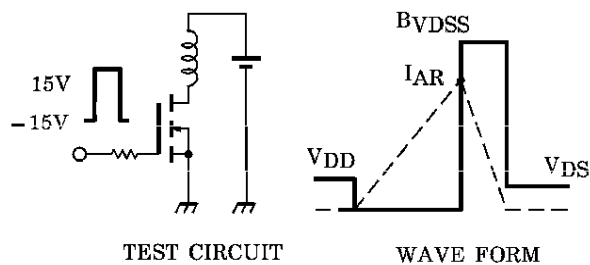
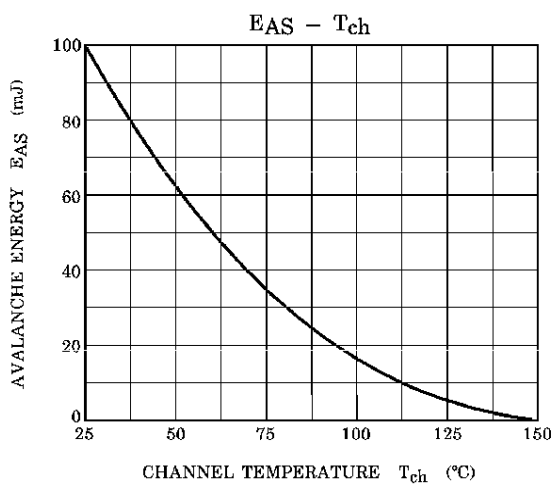
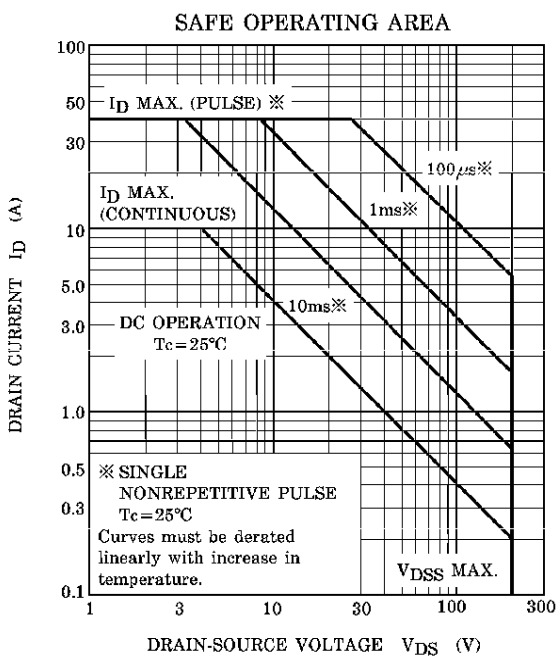
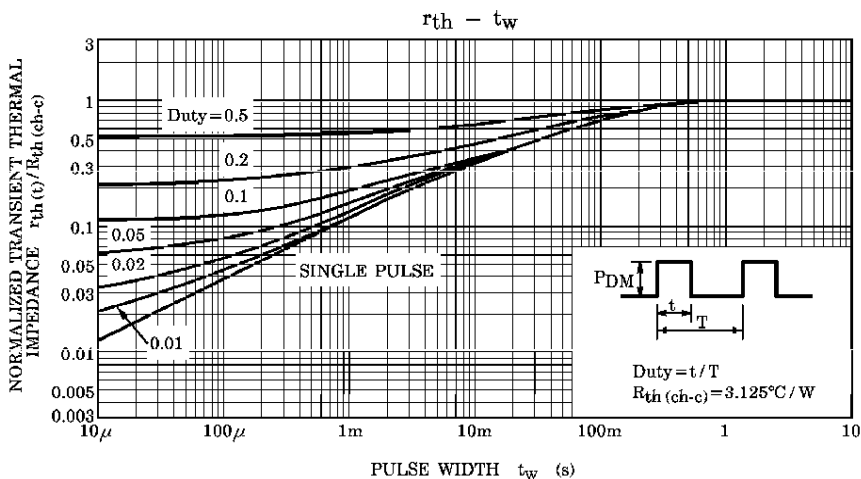
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Continuous Drain Reverse Current	I_{DR}	—	—	—	10	A
Pulse Drain Reverse Current	I_{DRP}	—	—	—	40	A
Diode Forward Voltage	V_{DSF}	$I_{DR} = 10A, V_{GS} = 0V$	—	—	-2.0	V
Reverse Recovery Time	t_{rr}	$I_{DR} = 10A, V_{GS} = 0V$ $dI_{DR} / dt = 100A / \mu s$	—	150	—	ns
Reverse Recovery Charge	Q_{rr}		—	0.8	—	μC

MARKING









Peak $I_{AR} = 10A$, $R_G = 25\Omega$
 $V_{DD} = 50V$, $L = 1.58mH$ $EAS = \frac{1}{2} \cdot L \cdot I^2 \cdot \left(\frac{BVDSS}{BVDSS - V_{DD}} \right)$